

BD433/5/7 BD434/6/8

COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The BD433, BD435, and BD437 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intented for use in medium power linear and switching applications. The BD433 is especially suitable for use in car-radio output stages.

The complementary PNP types are BD434, BD436, and BD438 respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value			Unit
	NPN		BD433	BD435	BD437	-
		PNP	BD434	BD436	BD438	-
V _{CBO}	Collector-Base Voltage (I _E = 0)		22	32	45	V
VCES	Collector-Emitter Voltage (V _{BE} = 0)		22	32	45	V
Vceo	Collector-Emitter Voltage (I _B = 0)		22	32	45	V
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$		5			V
Ι _C	Collector Current	llector Current		4		
I _{CM}	Collector Peak Current (t ≤ 10 ms)		7			Α
IB	Base Current		1		Α	
P _{tot}	Total Dissipation at $T_c \le 25 \ ^{\circ}C$		36			W
T _{stg}	Storage Temperature		-65 to 150			°C
Tj	Max. Operating Junction Temperature			°C		

For PNP types voltage and current values are negative.

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BD433 BD434 BD435 BD436 BD437 BD438

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	for BD433/434 for BD435/436 for BD437/438	V _{CB} = 22 V V _{CB} = 32 V V _{CB} = 45 V			100 100 100	μΑ μΑ μΑ
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for BD433/434 for BD435/436 for BD437/438	V _{CE} = 22 V V _{CE} = 32 V V _{CE} = 45 V			100 100 100	μΑ μΑ μΑ
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V				1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	for BD433/434 for BD435/436 for BD437/438	22 32 45			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 2 A	I _B = 0.2 A for BD433/434 for BD435/436 for BD437/438		0.2 0.2 0.2	0.5 0.5 0.6	V V V
V _{BE} *	Base-Emitter Voltage	I _C = 10 mA I _C = 2 A	V _{CE} = 5 V V _{CE} = 1 V for BD433/434 for BD435/436 for BD437/438		0.58	1.1 1.1 1.2	V V V V
hfe*	DC Current Gain	I _C = 10 mA I _C = 500 mA I _C = 2 A	$V_{CE} = 5 V$ for BD433/434 for BD435/436 for BD437/438 $V_{CE} = 1 V$ $V_{CE} = 1 V$ for BD433/434 for BD435/436 for BD437/438	40 40 30 85 50 50 40	130 130 130 140		
h _{FE1} /h _{FE2} *	Matched Pair	I _C = 500 mA	$V_{CE} = 1 V$			1.4	
f⊤	Transition frequency	I _C = 250 mA	$V_{CE} = 1 V$	3			MHz

 \ast Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

ЫМ	mm			inch			
Divi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	7.4		7.8	0.291		0.307	
В	10.5		10.8	0.413		0.425	
b	0.7		0.9	0.028		0.035	
b1	0.40		0.65	0.015		0.025	
С	2.4		2.7	0.094		0.106	
c1	1.0		1.3	0.039		0.051	
D	15.4		16.0	0.606		0.630	
е		2.2			0.087		
e3		4.4			0.173		
F		3.8			0.150		
G	3		3.2	0.118		0.126	
Н			2.54			0.100	
H2		2.15			0.084		
I		1.27			0.05		
0		0.3			0.011		
V		10 [°]			10 [°]		





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